Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method comprising:

orienting an interconnect with respect to a dense circuit device;

pressing the interconnect to the dense circuit device using a substrate; and

bonding the substrate to the dense circuit device sufficient to maintain the interconnect against the dense circuit device,

wherein the act of pressing comprises mechanically clamping the interconnect between the dense circuit device and the substrate.

2. (Previously Presented) The method of claim 1, wherein the act of orienting the interconnect comprises fitting a negative in the interconnect over a projection on the dense circuit device such that the negative receives and at least partially surrounds the projection.

3. (Original) The method of claim 1, wherein the act of orienting comprises orienting wires of the interconnect with electrical bond pads of the dense circuit device.

4. (Original) The method of claim 3, wherein the wires and the electrical bond pads overlap and at the overlap have a breadth from tens of nanometers to tens of microns.

5. (Original) The method of claim 3, wherein the wires and the electrical bond pads overlap and at the overlap have a space from tens of nanometers to tens of microns.

6. (Original) The method of claim 3, wherein the wires and the electrical bond pads overlap and at the overlap have a breadth of less than one micron.

7. (Original) The method of claim 3, wherein the wires and the electrical bond pads overlap and at the overlap have a space of less than one micron.

8. (Original) The method of claim 3, wherein the wires comprise copper.

9. (Original) The method of claim 1, wherein the act of bonding comprises covalently bonding the dense circuit device to the substrate.

10. (Withdrawn) The method of claim 1, wherein the act of bonding comprises ionic bonding of the dense circuit device to the substrate.

11. (Withdrawn) The method of claim 1, wherein the act of bonding comprises bonding the dense circuit device to the substrate using an adhesive.

12. (Original) The method of claim 1, wherein the act of bonding is performed at low temperature.

13. (Original) The method of claim 12, wherein the low temperature comprises room temperature.

14. (Original) The method of claim 1, further comprising:

covalently bonding wires of the interconnect with electrical bond pads of the dense circuit device.

15. (Original) The method of claim 1, wherein the dense circuit device comprises a length or width of less than or about twenty-five millimeters.

16. (Original) The method of claim 1, wherein the dense circuit device and the interconnect have different coefficients of thermal expansion.

17. (Original) The method of claim 1, wherein the substrate comprises a second dense circuit device.

18. (Previously Presented) The method of claim 1, further comprising:

fixing a spacer substrate to one of the dense circuit device or the substrate, and wherein the act of bonding comprises bonding the spacer substrate to an other of the dense circuit device or the substrate to which the spacer substrate is not yet fixed.

19. (Original) The method of claim 18, wherein the act of bonding comprises covalent, low-temperature bonding.

20. (Withdrawn) The method of claim 18, wherein the act of bonding comprises bonding with an adhesive.

21. (Original) The method of claim 18, wherein the substrate comprises a second dense circuit device and the spacer substrate comprises conductive vias to allow electrical communication between the dense circuit device and the second dense circuit device.

22. (Canceled)

23. (Canceled)

24. (Canceled)

25. (Original) A method comprising:

providing a dense circuit device having a first surface prepared for covalent bonding;

providing a substrate having a second surface prepared for covalent bonding;

orienting an interconnect between the dense circuit device and the substrate; and

mechanically clamping the interconnect between the dense circuit device and the substrate by covalently bonding the first surface to the second surface.

26. (Original) The method of claim 25, wherein the act of providing the dense surface device comprises preparing the first surface and the act of providing the substrate comprises preparing the second surface.

27. (Original) The method of claim 25, wherein the acts of providing the dense circuit device and providing the substrate comprise planarizing the first surface and the second surface.

28. (Previously Presented) The method of claim 25, wherein the dense circuit device comprises a projection comprising the first surface and the act of orienting comprises fitting a negative in the interconnect over the projection such that the negative receives and at least partially surrounds the projection.

29. (Previously Presented) The method of claim 25, wherein the substrate comprises a projection comprising the second surface and the act of orienting comprises fitting a negative in the interconnect over the projection such that the negative receives and at least partially surrounds the projection.

30. (Withdrawn) The method of claim 25, wherein the act of orienting comprises placing the interconnect between two or more guides.

31. (Original) The method of claim 25, wherein the act of orienting comprises orienting wires of the interconnect with electrical bond pads of the dense circuit device.

32. (Original) The method of claim 31, wherein the wires and the electrical bond pads overlap and at the overlap have a breadth from about tens of nanometers to tens of microns.

33. (Original) The method of claim 31, wherein the wires and the electrical bond pads overlap and at the overlap have a breadth of less than one micron.

34. (Original) The method of claim 25, wherein the act of orienting comprises stiffening the interconnect.

35. (Original) The method of claim 25, wherein the act of mechanically clamping is performed at low temperature.

36. (Original) The method of claim 35, wherein the low temperature comprises room temperature.

37. (Original) The method of claim 25, further comprising forming a compliant layer between the interconnect and the substrate.

38. (Original) The method of claim 25, wherein the interconnect includes wires and a compliant layer.

39. (Original) The method of claim 25, wherein the interconnect includes wires, a compliant layer, and a stiffening layer.

40. (Withdrawn) The method of claim 25, wherein the interconnect includes grouped wires and an insulative layer.

41. (Original) The method of claim 25, wherein the first surface and the second surface comprise a silicon-containing material.

42. (Original) The method of claim 25, wherein the substrate comprises a second dense circuit device.

43. (Original) The method of claim 42, wherein the substrate and the first dense circuit device are separated by a spacer having conductive vias enabling electrical communication between the second dense circuit device and the first dense circuit device.

44. (Previously Presented) A method comprising:

planarizing a first surface of a dense circuit device;

planarizing a second surface of a spacer substrate;

planarizing a third surface of the spacer substrate;

planarizing a fourth surface of a clamping substrate;

covalently bonding one of the (a) first surface to the second surface or (b) the third surface to the fourth surface;

orienting an interconnect between the dense circuit device and the clamping substrate; and

mechanically clamping the interconnect to the dense circuit device by covalently bonding an other of the (a) first surface to the second surface or (b) the third surface to the fourth surface.

45. (Original) The method of claim 44, wherein the act of mechanically clamping is performed at low temperature.

46. (Original) The method of claim 44, wherein the dense circuit device comprises a dimension of less than or about twenty-five millimeters.

47. (Original) The method of claim 44, wherein the clamping substrate comprises a second dense circuit device.

48. (Original) The method of claim 47, wherein the interconnect comprises two sets of wires, the first set contacting the first dense circuit device and the second set contacting the second dense circuit device.

49-86 (Canceled)

87. (Previously Presented) The method of claim 25 further comprising:

preparing the first surface for covalent bonding and preparing the second surface for covalent bonding.

88. (Currently Amended) The method of claim 87, wherein the dense circuit device has a projection including the first surface and wherein the interconnect has a hole ~~depression~~ form by the second surface and wherein orienting the interconnect between the dense circuit device and the substrate includes orienting the projection in the hole ~~depression~~.

89. (Currently Amended) The method of claim 88, wherein the ~~depression~~ hole is generally a negative of the projection.

90. (Previously Presented) The method of claim 88, wherein the act of orienting comprises orienting electrical bond pads of the dense circuit device with wires of the interconnect.

91. (Previously Presented) The method of claim 90, wherein the dense circuit device has a length or width of less than or about twenty-five millimeters and the electrical bond pads or the wires are less than one micron in breadth.

92. (Previously Presented) The method of claim 90, wherein the dense circuit device has a length or width of less than or about five millimeters and the electrical bond pads or the wires are less than or about ten microns in breadth.

93. (Previously Presented) The method of claim 90, wherein the act of covalently bonding mechanically bonds wires of the interconnect with electrical bond pads of the dense circuit device.